
 $^{170}\text{Ir } \varepsilon \text{ decay (0.87 s)}$ [2001Ki10](#),[2002Ro17](#)

Type	Author	History	Citation	Literature Cutoff Date
Full Evaluation	C. M. Baglin ¹ , E. A. Mccutchan ² , S. Basunia ¹		NDS 153, 1 (2018)	1-Oct-2018

Parent: ^{170}Ir : E=0.0; $J^\pi=(3^-)$; $T_{1/2}=0.87$ s +18–12; $Q(\varepsilon)=10567$ SY; % ε +% β^+ decay=94.8 17

^{170}Ir -Q(ε): 10567 (syst) 89 ([2017Wa10](#)).

^{170}Ir -% ε +% β^+ decay: from (100-% α), where % α =5.2 17 (from [2002Ro17](#)).

[2001Ki10](#): ^{170}Ir source produced using $^{144}\text{Sm}(^{31}\text{P},5\text{n})$, E(^{31}P)=150 MeV for use in a study of the ε decay of the ^{170}Re granddaughter. No details are reported for $^{170}\text{Ir } \varepsilon$ decay ([2001Ki10](#)).

[2002Ro17](#): ^{170}Ir parent produced In sequential α decay of ^{178}Tl and ^{174}Au ; Si strip detector; measured E α , parent-daughter α correlations; ε decay of ^{170}Ir inferred from observed intensity of $^{170}\text{Os } \alpha$ decay after making allowance for ^{170}Os production via the alternative $^{178}\text{Tl}(\alpha)-^{174}\text{Au}(\varepsilon)-^{174}\text{Pt}(\alpha)-^{170}\text{Os}$ sequence.

 ^{170}Os Levels

E(level)	J^π
0.0	0^+